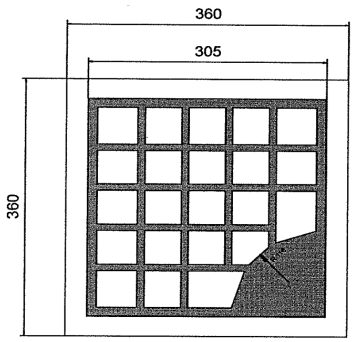
EPIGAP Optronic GmbH
Koepenicker Str. 325b
D-12555 Berlin
Fon: +49 (0)30 657637 60
Fax: +49 (0)30 657637 70

Data Sheet

LED Chip Infrared EOLC-1720-17-1

Rev. 03, 2017

Radiation	Type	Electrodes
Infrared	InGaAs, MQW	P (anode) up



typ. dimensions (µm)

typ. thickness: 260 µm

anode: gold alloy, 1.5 µm

cathode: gold alloy, 0.5 µm

Maximum Ratings

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I_F			100	mA
Peak forward current	$t_p \leq$ 50 µs, t_p/T=½	I_{FM}			200	mA

Optical and Electrical Characteristics

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=20 mA	V_F		0.7		V
Forward voltage	I_F=100 mA	V_F		0.9		V
Reverse voltage	I_R=100 µA	V_R	5			V
Radiant power*	I_F=20 mA	Φ_e		0.8		mW
Radiant power*	I_F=100 mA	Φ_e		2.8		mW
Peak wavelength	I_F=20 mA	λ_p		1720		nm
FWHM	I_F=20 mA	$\Delta\lambda_{0.5}$		100		nm
Switching time	I_F=20 mA	t_r, t_f		10		ns

*Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire-bond side top

Art. No. 113 042

We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.